

Amendments to the Claim

Claims 1-61 (Cancelled).

62. (Original) A method of forming a semiconductor construction, comprising:
forming a dielectric material over a semiconductive substrate material;
patterning the dielectric material to form at least two patterned blocks, a pair of adjacent blocks being separated by a first gap, each block having a sidewall within the first gap;
forming a pair of spacers along the sidewalls and within the first gap, the spacers having lateral edges separated by a gap, the second gap being narrower than the first gap;
while the spacers remain along the sidewalls, implanting at least one dopant into the semiconductive material within the second gap to form a doped region; and
removing the spacers from along the sidewalls.

63. (Original) The method of claim 62 further comprising after removing the spacers, forming a layer of polysilicon over the semiconductive material within the gap and along the sidewalls.

64. (Original) The method of claim 63 further comprising:
depositing a material comprising at least one of a metal and a metal nitride over the polysilicon layer; and

planarizing the material.

65. (New) The method of claim 64 wherein the material comprises tungsten.

66. (New) The method of claim 62 wherein the at least one dopant comprises indium.

67. (New) The method of claim 62 wherein the second gap is less than or equal to half the width of the first gap.